# BLL8H1214L-500; BLL8H1214LS-500 LDMOS L-band radar power transistor Rev. 3 — 1 September 2015

**AMPLEON** 

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

500 W LDMOS power transistor intended for L-band radar applications in the 1.2 GHz to 1.4 GHz range.

#### **Test information** Table 1.

Typical RF performance at  $T_{case} = 25$  °C;  $t_D = 300 \ \mu s$ ;  $\delta = 10$  %;  $I_{Dq} = 150 \ mA$ ; in a class-AB production test circuit.

Test signal	f	V <sub>DS</sub>	$P_L$	G <sub>p</sub>	$\eta_{D}$	t <sub>r</sub>	t <sub>f</sub>
	(GHz)	(V)	(W)	(dB)	(%)	(ns)	(ns)
pulsed RF	1.2 to 1.4	50	500	17	50	20	6

#### 1.2 Features and benefits

- Easy power control
- Integrated dual side ESD protection
- High flexibility with respect to pulse formats
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1.2 GHz to 1.4 GHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

#### 1.3 Applications

 L-band power amplifiers for radar applications in the 1.2 GHz to 1.4 GHz frequency range

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	e Graphic symbol
BLL8H1214	4L-500 (SOT539A)		
1	drain1		
2	drain2	1 2	
3	gate1		5 3
4	gate2	3 4	5
5	source	[1]	4 —
			ب "ا
			2 sym117
BLL8H1214	4LS-500 (SOT539B)		
1	drain1		
2	drain2	1 2	1
3	gate1	5	⊷
4	gate2	3 4	3——5
5	source	[1]	4 7
			"┡─┐
			2 sym117

<sup>[1]</sup> Connected to flange.

## 3. Ordering information

Table 3. Ordering information

Type number	Packag	Package				
	Name	Description	Version			
BLL8H1214L-500	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A			
BLL8H1214LS-500	-	earless flanged balanced ceramic package; 4 leads	SOT539B			

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	100	V
$V_{GS}$	gate-source voltage		-6	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
Z <sub>th(j-c)</sub>	transient thermal impedance from	T <sub>case</sub> = 85 °C; P <sub>L</sub> = 500 W		
	junction to case	$t_p$ = 100 $\mu$ s; $\delta$ = 10 %	0.046	K/W
		$t_p$ = 200 $\mu$ s; $\delta$ = 10 %	0.059	K/W
		$t_p$ = 300 $\mu$ s; $\delta$ = 10 %	0.069	K/W
		$t_p$ = 100 $\mu$ s; $\delta$ = 20 %	0.064	K/W

#### 6. Characteristics

#### Table 6. DC characteristics

 $T_i = 25$  °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.7 \text{ mA}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 270 mA	1.3	1.8	2.2	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	32	42	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 270 mA	1.7	3	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 9.5 \text{ A}$	-	100	164	mΩ

#### Table 7. RF characteristics

Test signal: pulsed RF;  $t_p$  = 300  $\mu$ s;  $\delta$  = 10 %; RF performance at  $V_{DS}$  = 50 V;  $I_{Dq}$  = 150 mA;  $T_{case}$  = 25 °C; unless otherwise specified, in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	P <sub>L</sub> = 500 W	-	-	50	V
Gp	power gain	P <sub>L</sub> = 500 W	15	17	-	dB
RLin	input return loss	P <sub>L</sub> = 500 W	-	-10	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		-	600	-	W
η <sub>D</sub>	drain efficiency	P <sub>L</sub> = 500 W	45	50	-	%
P <sub>droop(pulse)</sub>	pulse droop power	P <sub>L</sub> = 500 W	-	0	0.3	dB
t <sub>r</sub>	rise time	P <sub>L</sub> = 500 W	-	20	50	ns
t <sub>f</sub>	fall time	P <sub>L</sub> = 500 W	-	6	50	ns

#### 7. Test information

#### 7.1 Ruggedness in class-AB operation

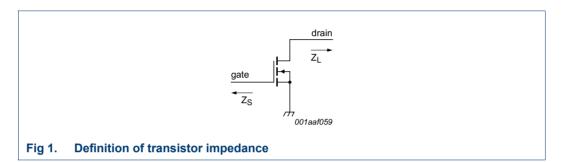
The BLL8H1214L-500 and BLL8H1214LS-500 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V;  $I_{Dq}$  = 150 mA;  $P_L$  = 500 W;  $t_p$  = 300  $\mu$ s;  $\delta$  = 10 %.

## 7.2 Impedance information

Table 8. Typical impedance

Typical values per section unless otherwise specified.

f	Z <sub>S</sub>	Z <sub>L</sub>
(GHz)	(Ω)	(Ω)
1.2	1.268 – j2.623	2.987 – j1.664
1.3	2.193 – j2.457	2.162 – j1.326
1.4	2.359 – j2.052	1.604 – j1.887



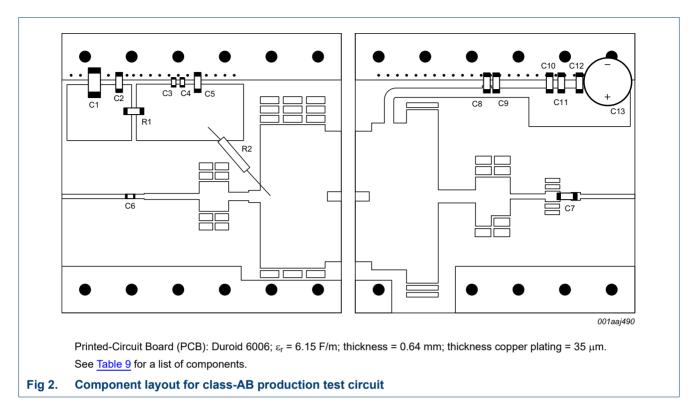
#### 7.3 Test circuit

Table 9. List of components

For test circuit see Figure 2.

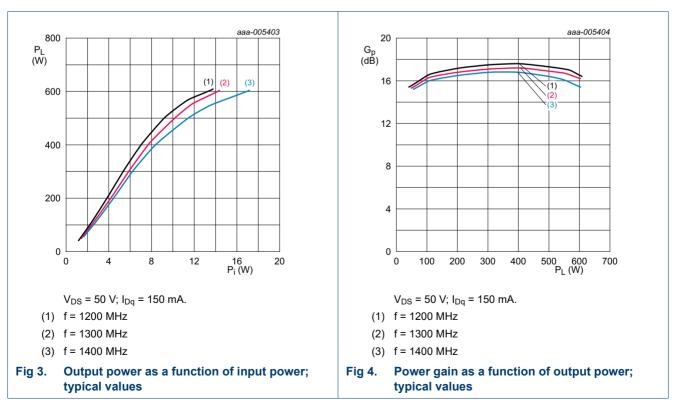
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	22 μF, 35 V	
C2	multilayer ceramic chip capacitor	51 pF [1]	
C3, C4	multilayer ceramic chip capacitor	100 pF [1]	
C5, C11, C12	multilayer ceramic chip capacitor	1 nF [2]	
C6	multilayer ceramic chip capacitor	47 pF [1]	
C7, C8, C10	multilayer ceramic chip capacitor	51 pF [3]	
C9	multilayer ceramic chip capacitor	100 pF [3]	
C13	electrolytic capacitor	10 μF, 63 V	
R1	SMD resistor	56 Ω	SMD 0603
R2	metal film resistor	51 Ω	

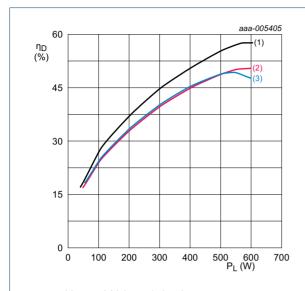
- [1] American Technical Ceramics type 100A or capacitor of same quality.
- [2] American Technical Ceramics type 100B or capacitor of same quality.
- [3] American Technical Ceramics type 800B or capacitor of same quality.



## 7.4 RF performance graphs

## 7.4.1 Performance curves measured with $\delta$ = 10 %, $t_p$ = 300 $\mu$ s and $T_h$ = 25 °C

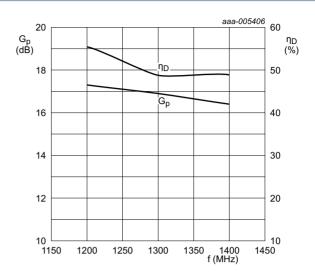




 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

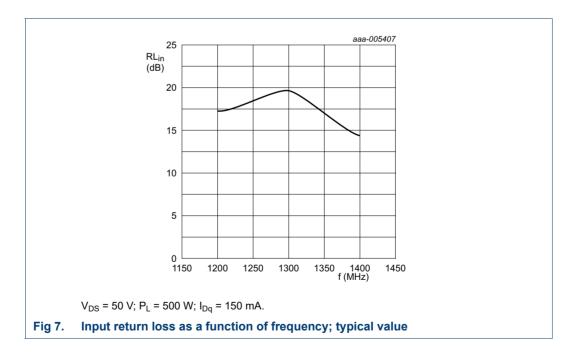
- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 5. Drain efficiency as a function of output power; typical values

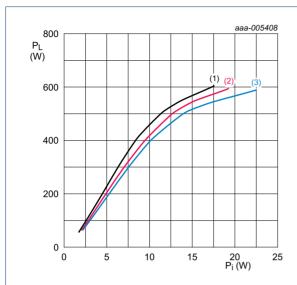


 $V_{DS}$  = 50 V;  $P_{L}$  = 500 W;  $I_{Dq}$  = 150 mA.

Fig 6. Power gain and drain efficiency as function of frequency; typical values



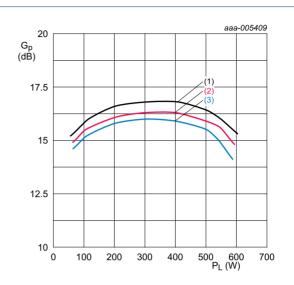
#### 7.4.2 Performance curves measured with $\delta$ = 10 %, $t_p$ = 300 $\mu$ s and $T_h$ = 65 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

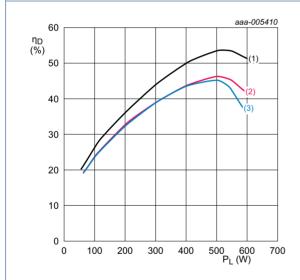
Fig 8. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

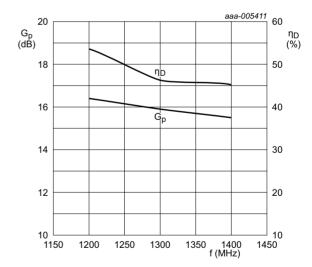
Fig 9. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 100 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

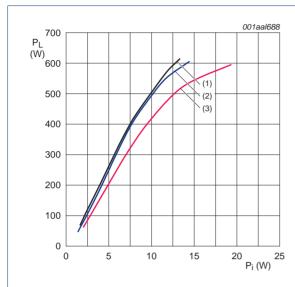
Fig 10. Drain efficiency as a function of output power; typical values



 $V_{DS} = 50 \text{ V}$ ;  $P_L = 500 \text{ W}$ ;  $I_{Dq} = 100 \text{ mA}$ .

Fig 11. Power gain and drain efficiency as function of frequency; typical values

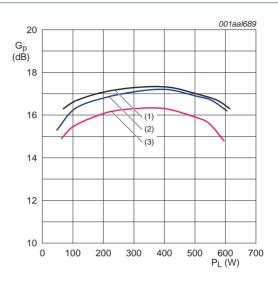
#### 7.4.3 Performance curves measured with $\delta$ = 10 %, $t_p$ = 300 $\mu$ s and f = 1300 MHz



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1)  $T_h = -40 \, ^{\circ}C$
- (2)  $T_h = +25 \, ^{\circ}C$
- (3)  $T_h = +65 \, ^{\circ}C$

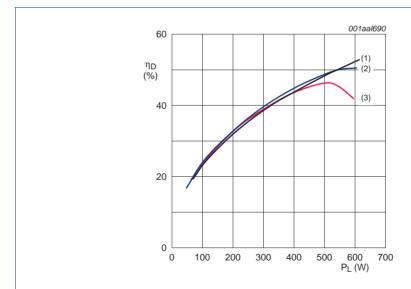
Fig 12. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V;} I_{Dq} = 150 \text{ mA}.$ 

- (1)  $T_h = -40 \, ^{\circ}C$
- (2)  $T_h = +25 \, ^{\circ}C$
- (3)  $T_h = +65 \, ^{\circ}C$

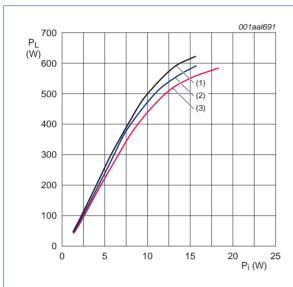
Fig 13. Power gain as a function of output power; typical values



- (1)  $T_h = -40 \, ^{\circ}C$
- (2)  $T_h = +25 \, ^{\circ}C$
- (3)  $T_h = +65 \, ^{\circ}C$

Fig 14. Drain efficiency as a function of output power; typical values

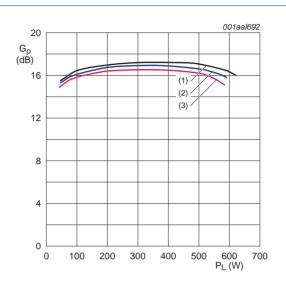
#### 7.4.4 Performance curves measured with $\delta$ = 20 %, $t_p$ = 500 $\mu$ s and $T_h$ = 25 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

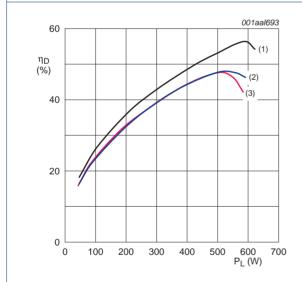
Fig 15. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 16. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 17. Drain efficiency as a function of output power; typical values

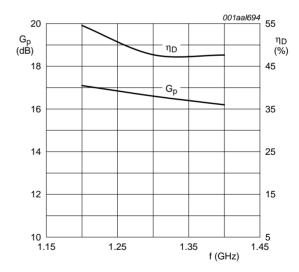
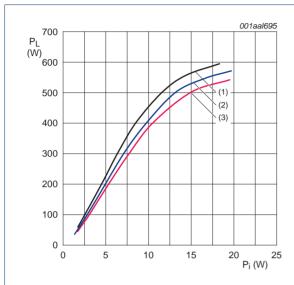


Fig 18. Power gain and drain efficiency as function of frequency; typical values

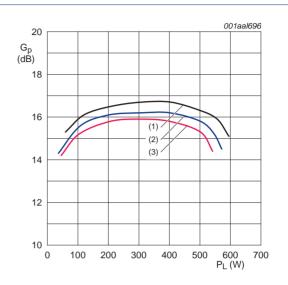
#### 7.4.5 Performance curves measured with $\delta$ = 20 %, $t_p$ = 500 $\mu$ s and $T_h$ = 65 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

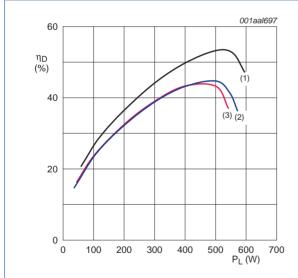
Fig 19. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 20. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 21. Drain efficiency as a function of output power; typical values

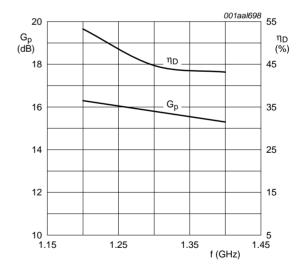
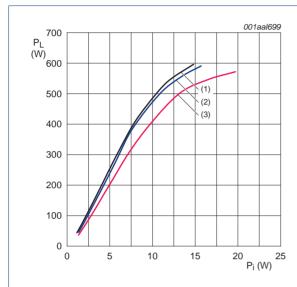


Fig 22. Power gain and drain efficiency as function of frequency; typical values

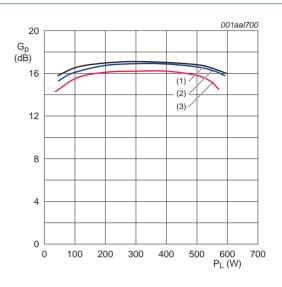
#### 7.4.6 Performance curves measured with $\delta$ = 20 %, $t_p$ = 500 $\mu$ s and f = 1300 MHz



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1)  $T_h = -40 \, ^{\circ}C$
- (2) T<sub>h</sub> = +25 °C
- (3)  $T_h = +65 \, ^{\circ}C$

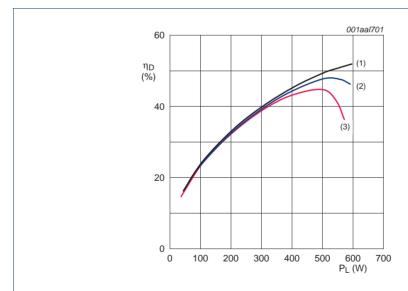
Fig 23. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1)  $T_h = -40 \, ^{\circ}C$
- (2)  $T_h = +25 \, ^{\circ}C$
- (3)  $T_h = +65 \, ^{\circ}C$

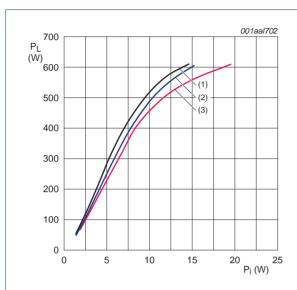
Fig 24. Power gain as a function of output power; typical values



- (1)  $T_h = -40 \, ^{\circ}C$
- (2)  $T_h = +25 \, ^{\circ}C$
- (3)  $T_h = +65 \, ^{\circ}C$

Fig 25. Drain efficiency as a function of output power; typical values

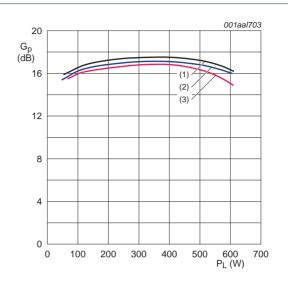
#### 7.4.7 Performance curves measured with $\delta$ = 10 %, $t_p$ = 1 ms and $T_h$ = 25 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

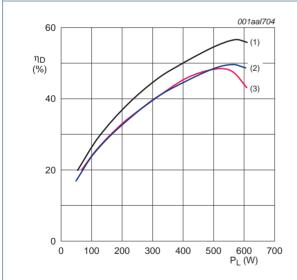
Fig 26. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 27. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 28. Drain efficiency as a function of output power; typical values

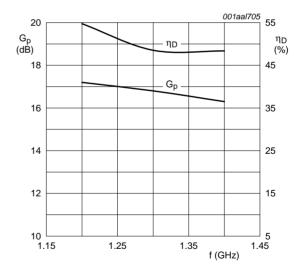
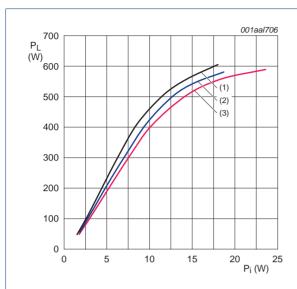


Fig 29. Power gain and drain efficiency as function of frequency; typical values

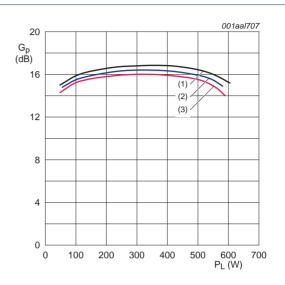
#### 7.4.8 Performance curves measured with $\delta$ = 10 %, $t_p$ = 1 ms and $T_h$ = 65 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

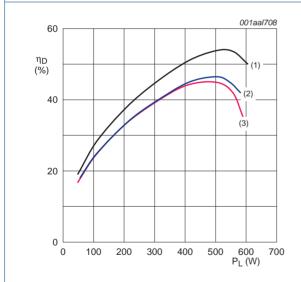
Fig 30. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 31. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 32. Drain efficiency as a function of output power; typical values

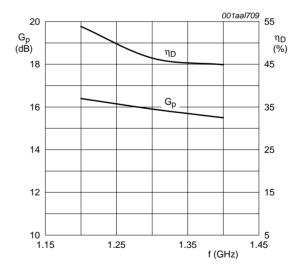
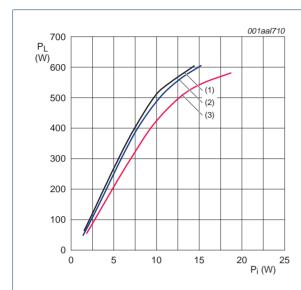


Fig 33. Power gain and drain efficiency as function of frequency; typical values

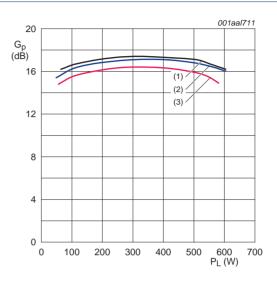
## 7.4.9 Performance curves measured with $\delta$ = 10 %, $t_p$ = 1 ms and f = 1300 MHz



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1)  $T_h = -40 \, ^{\circ}C$
- (2)  $T_h = +25 \, ^{\circ}C$
- (3)  $T_h = +65 \, ^{\circ}C$

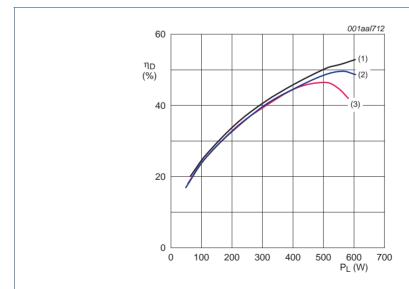
Fig 34. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$ 

- (1)  $T_h = -40 \, ^{\circ}C$
- (2)  $T_h = +25 \, ^{\circ}C$
- (3)  $T_h = +65 \,^{\circ}C$

Fig 35. Power gain as a function of output power; typical values



- (1)  $T_h = -40 \, ^{\circ}C$
- (2)  $T_h = +25 \, ^{\circ}C$
- (3)  $T_h = +65 \, ^{\circ}C$

Fig 36. Drain efficiency as a function of output power; typical values

## 8. Package outline

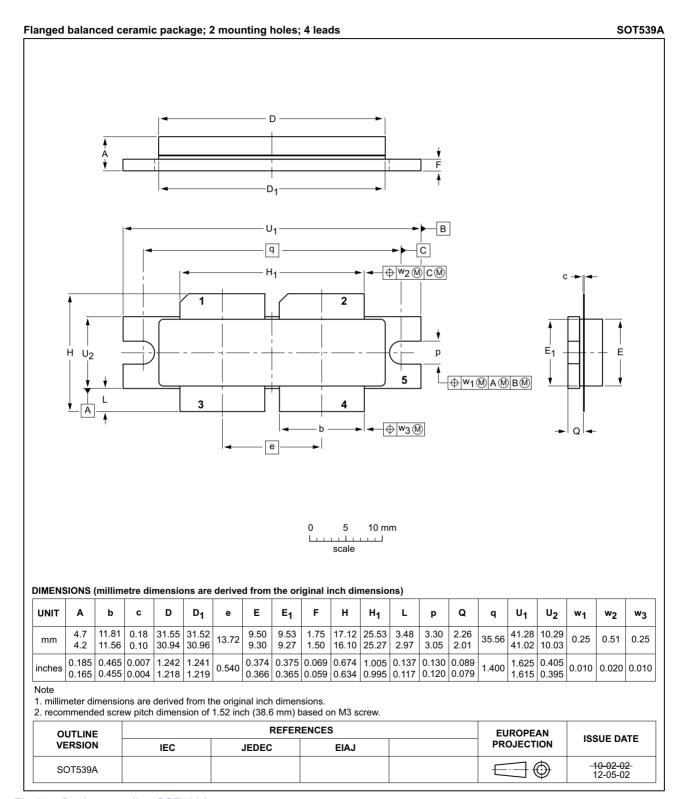


Fig 37. Package outline SOT539A

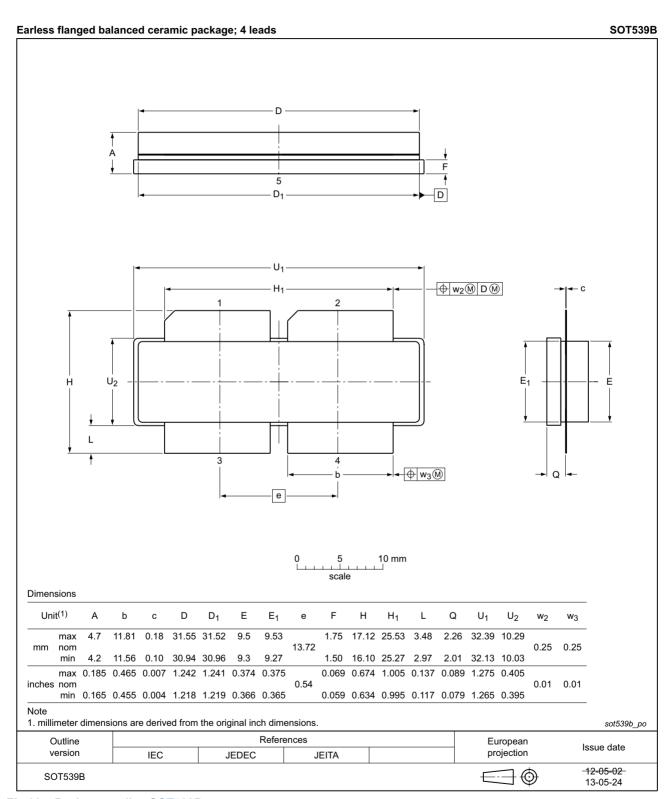


Fig 38. Package outline SOT539B

## 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

## 10. Abbreviations

Table 10. Abbreviations

Acronym	Description	
ESD	ElectroStatic Discharge	
L-band	Long wave Band	
LDMOS	Laterally Diffused Metal-Oxide Semiconductor	
MTF	Median Time to Failure	
SMD	Surface Mounted Device	
VSWR	Voltage Standing-Wave Ratio	

## 11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLL8H1214L-500_1214LS-500 #3	20150901	Product data sheet	-	BLL8H1214L-500_1214LS-500 #2	
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
BLL8H1214L-500_1214LS-500 #2	20150209	Product data sheet	-	BLL8H1214L-500_1214LS-500 #1	
BLL8H1214L-500_1214LS-500 #1	20140930	Objective data sheet	-	-	

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition	
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.	
Product [short] data sheet	Production	This document contains the product specification.	

- [1] Please consult the most recently issued document before initiating or completing a design.
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## LDMOS L-band radar power transistor

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